

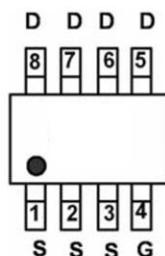
## GENERAL FEATURES

- $V_{DS} = -60V$   $I_D = -4A$
- $R_{DS(ON)} < 98m\Omega$  @  $V_{GS}=10V$
- $R_{DS(ON)} < 145m\Omega$  @  $V_{GS}=4.5V$

## Application

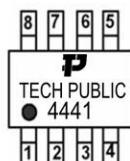
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

## Package and Pin Configuration



SOP-8 top view

Marking:



## Circuit diagram



## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-60	V
Continuous Drain Current	$I_D$	-4	A
Pulsed Drain Current (note1)	$I_{DM}$	-16	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	36	mJ
Avalanche Current	$I_{As}$	12	A
Power Dissipation ( $T_C = 25^\circ C$ ) (note3)	$P_D$	3.1	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 To 150	°C

## Thermal Data

Symbol	Parameter	Value	Unit
$R_{thj-a}$	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 40	°C/W

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$  unless otherwise noted)**

<b>Specifications</b> $T_J = 25^\circ\text{C}$ , unless otherwise noted						
<b>Parameter</b>	<b>Symbol</b>	<b>Test Conditions</b>	<b>Value</b>			<b>Unit</b>
			<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-60	--	--	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = -60\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	-1	$\mu\text{A}$
		$V_{\text{DS}} = -60\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 150^\circ\text{C}$	--	--	-100	
Gate-Source Leakage	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 20\text{V}$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-1.0	-1.7	-3.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, I_D = -4\text{A}$	--	90	98	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_D = -3\text{A}$	--	100	145	$\text{m}\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = -30\text{V}, f = 1.0\text{MHz}$	--	976	--	$\text{pF}$
Output Capacitance	$C_{\text{oss}}$		--	70	--	
Reverse Transfer Capacitance	$C_{\text{rss}}$		--	30	--	
Total Gate Charge	$Q_g$	$V_{\text{DD}} = -30\text{V}, I_D = -4\text{A}, V_{\text{GS}} = -10\text{V}$	--	24	--	$\text{nC}$
Gate-Source Charge	$Q_{\text{gs}}$		--	2.2	--	
Gate-Drain Charge	$Q_{\text{gd}}$		--	3.6	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = -30\text{V}, I_D = -4\text{A}, R_G = 2.5\Omega$	--	10	--	$\text{ns}$
Turn-on Rise Time	$t_r$		--	5	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	35	--	
Turn-off Fall Time	$t_f$		--	9	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_s$	$T_C = 25^\circ\text{C}$	--	--	-4	$\text{A}$
Pulsed Diode Forward Current	$I_{\text{SM}}$		--	--	-16	
Body Diode Voltage	$V_{\text{SD}}$	$T_J = 25^\circ\text{C}, I_{\text{SD}} = -4\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	-1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = -4\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	36	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	38	--	nC



**TECH PUBLIC**

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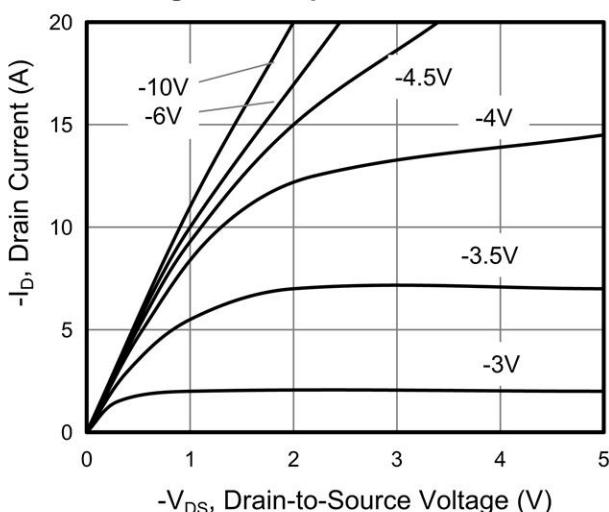
**AO4441**

**P-Channel Enhancement Mode MOSFET**

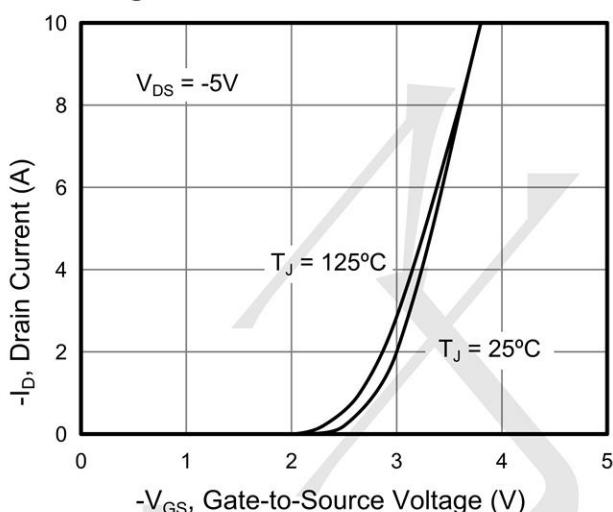
[www.sot23.com.tw](http://www.sot23.com.tw)

### Typical Electrical and Thermal Characteristics

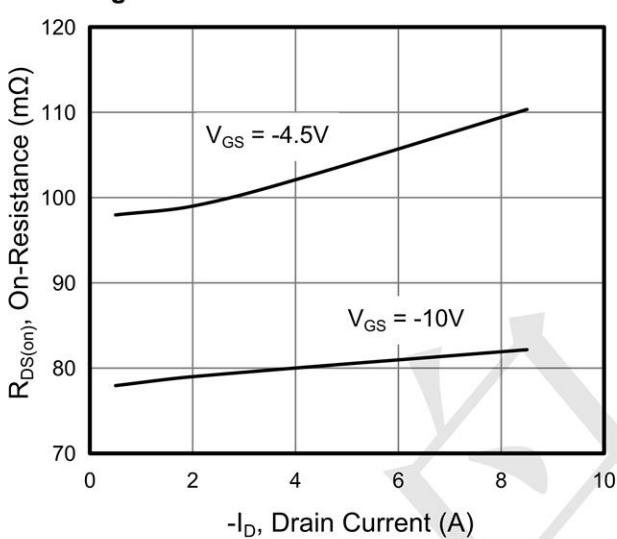
**Figure 1. Output Characteristics**



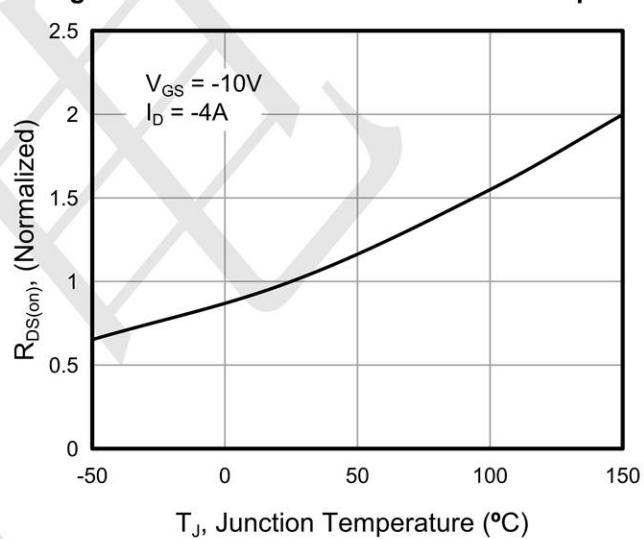
**Figure 2. Transfer Characteristics**



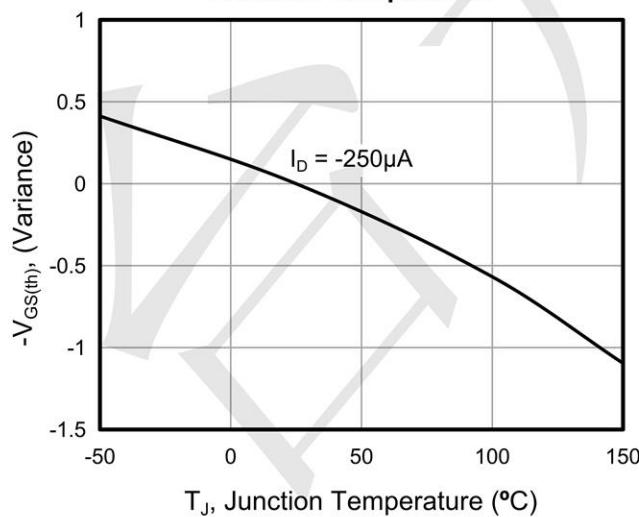
**Figure 3. On-Resistance vs. Drain Current**



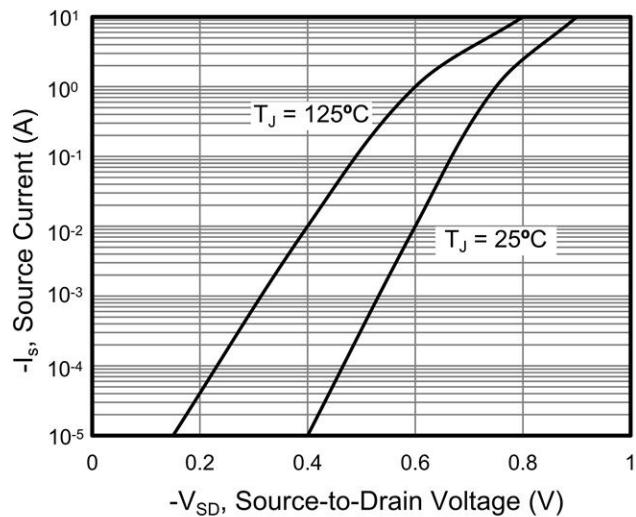
**Figure 4. On-Resistance vs. Junction Temperature**



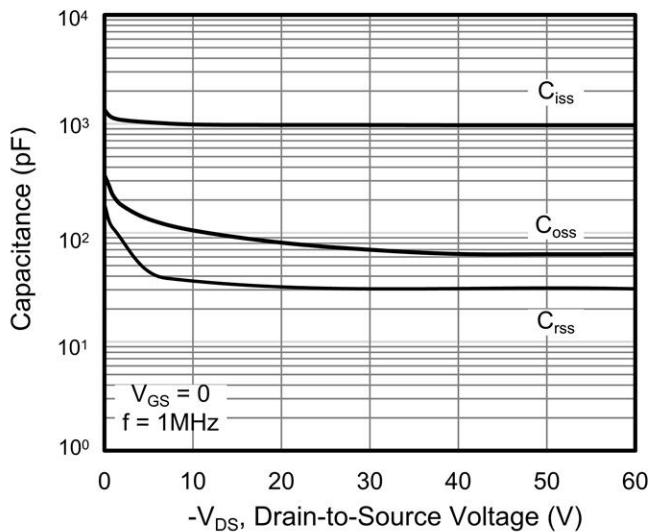
**Figure 5. Threshold Voltage vs. Junction Temperature**



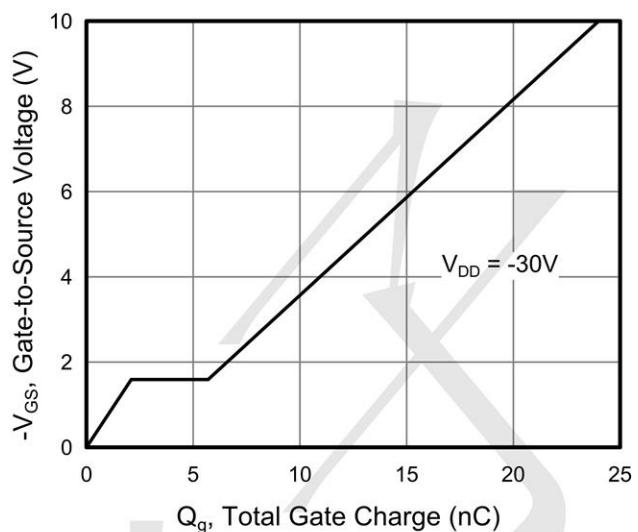
**Figure 6. Body Diode Forward Voltage**



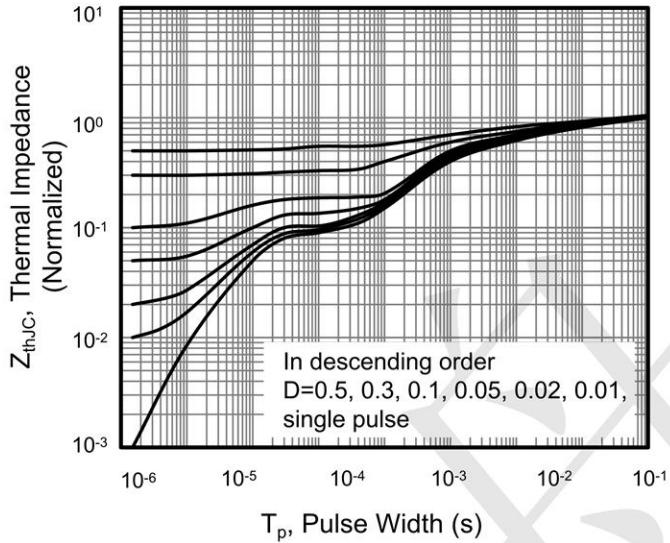
**Figure 7. Capacitance**



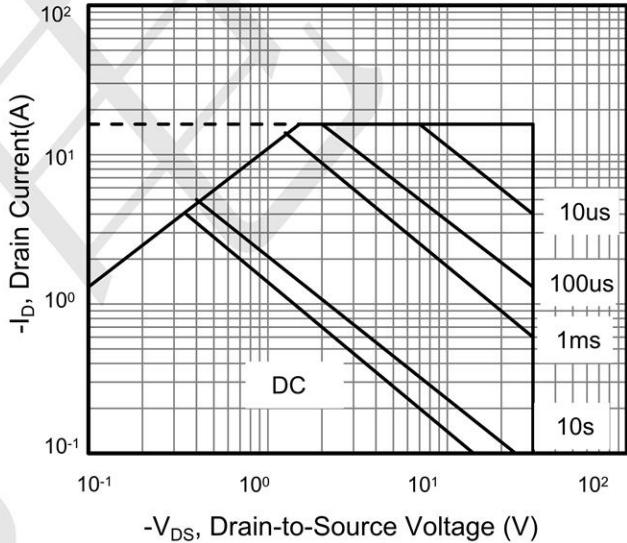
**Figure 8. Gate Charge**



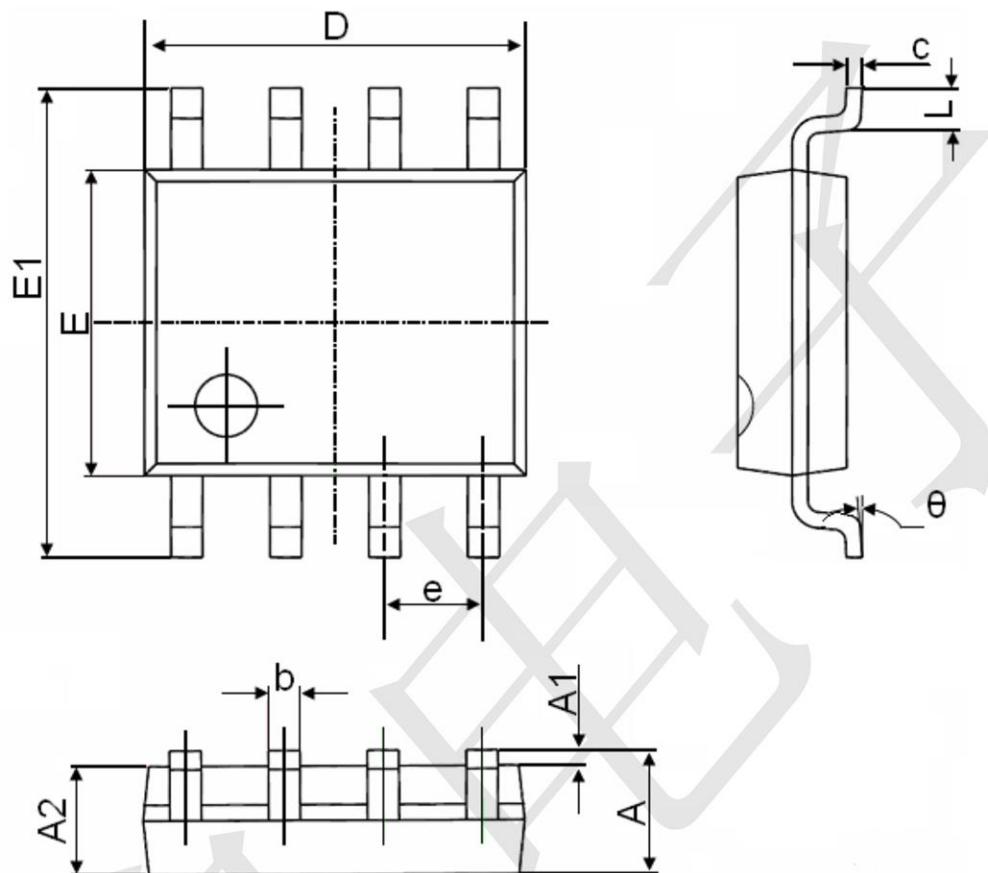
**Figure 9. Transient Thermal Impedance**



**Figure 10. Safe Operating Area**



**SOP-8 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°